

FORM PTO-1449 (SUBSTITUTE)  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))				Attorney Docket No.:      Serial No. <b>GR 99 P 4724 US</b> <b>09/677,545</b>  Applicant <b>Martin Schrems et al.</b>  Filing Date                      Group Art Unit <b>October 2, 2000</b>			
U.S. PATENT DOCUMENTS							
EXAMINER INITIALS	PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE	
<i>cn</i>	A	4,937,205	06/26/90	Nakayama et al.		/	
<i>cn</i>	B	5,189,503	02/23/93	Suguro et al.			
<i>cn</i>	C	5,250,829	10/05/93	Bronner et al.			
<i>cn</i>	D	5,344,381	09/06/94	Cabrera y Lopez Caram			
	E						
	F						
	G						
	H						
	I						
FOREIGN PATENT DOCUMENT							
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES   NO	
	J	/					
	K						
	L						
	M						
	N						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>cn</i>	O	Frank S. Becker et al.: "Low Pressure Deposition of Doped SiO <sub>2</sub> by Pyrolysis of Tetraethylorthosilicate (TEOS)", Journal of the Electrochemical Society, Vol. 136, No. 10, October 1989, pp. 3033-3043;					
<i>cn</i>	P	C.N.Ransom et al.: "Shallow n <sup>+</sup> Junctions in Silicon by Arsenic Gas-Phase Doping", Journal of the Electrochemical Society, Vol. 141, No. 5, May 1994, pp. 1378-1381					
EXAMINER <i>Gregory</i>				DATE CONSIDERED <i>6-19-02</i>			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							